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## **Electronic Supplementary Information**

MOF-derived hierarchical core-shell hollow  $Co_3S_4$  (a)Ni $Co_2O_4$  nanosheet arrays for asymmetric supercapacitors

Ye Tian,<sup>‡</sup><sup>a</sup> Zhigao Xue,<sup>‡</sup><sup>a</sup> Qingqing Zhao,<sup>a</sup> Jie Guo,<sup>\*a</sup> Kai Tao<sup>\*a</sup>and Lei Han<sup>a</sup>

<sup>a</sup>School of Materials Science & Chemical Engineering, Ningbo University, Ningbo, Zhejiang 315211, China.

Email: taokai@nbu.edu.cn; guojie@nbu.edu.cn.

## **Electrochemical calculation**

The specific capacitance (C<sub>s</sub>, F/cm<sup>2</sup>) of the electrode material is calculated by following equation:

$$C_{s} = \frac{I \times \Delta t}{S \times \Delta V} (1)$$

where I (A),  $\Delta t$  (s),  $\Delta V$  (V) and S (cm<sup>2</sup>) are the discharging current, discharging time, voltage window for charge-discharge process and area of active materials, respectively.

The specific capacitance (C<sub>s</sub>, F/g) of the electrode material is calculated by following equation:

$$C_{s} = \frac{I \times \Delta t}{m \times \Delta V}$$
(2)

where I (A),  $\Delta t$  (s),  $\Delta V$  (V) and m (g) are the discharging current, discharging time, voltage window for charge-discharge process and mass of active materials, respectively.

The charge storage mechanism and reaction kinetics ware analysed by the formula as follows:

$$i = av^{b}_{(3)}$$

where I (A), v (mV s<sup>-1</sup>), a value and b value are peak curren, scan rate, constant and constant, respectively. When b = 0.5, the material storage mechanism is considered as battery type. When b=1, the material storage mechanism is considered as capacitive character.

The capacitive  $(k_1v)$  and diffusion-controlled  $(k_2v^{1/2})$  currents are separated by following equation:

$$i = k_1 v + k_2 v^{1/2}$$
 (4)

In the two-electrode test, the positive and negative charges should be balanced, so the mass of positive and negative substances is as follows:

$$\mathbf{Q}_{-} = \mathbf{m}_{-} \times \mathbf{C}_{-} \times \Delta \mathbf{V}_{-} = \mathbf{m}_{+} \times \mathbf{C}_{+} \times \Delta \mathbf{V}_{+} = \mathbf{Q}_{+}$$
(5)

Where m (g), C (F/g) and  $\Delta V$  (V) are active materials, specific capacitance, and charge-discharge voltage of positive and negative electrodes, respectively.

The energy density (E, Wh/kg) and power density (W/kg) calculation equation of  $Co_3S_4@NiCo_2O_4/rGO/NF//AC/NF$  cell is as follows:

$$E = \frac{C_s \times (\Delta V)^2}{2 \times 3.6}$$
(6)  
$$P = \frac{3600 \times E}{\Delta t}$$
(7)

Where C (F/g),  $\Delta t$  (s) and  $\Delta V$  (V) are specific capacitance, discharging time and working voltage of Co<sub>3</sub>S<sub>4</sub>@NiCo<sub>2</sub>O<sub>4</sub>/rGO/NF//AC/NF cell, respectively.

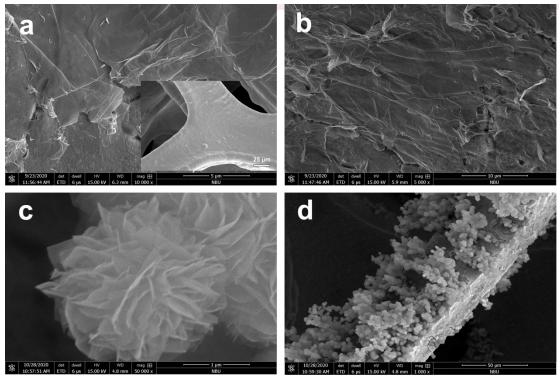
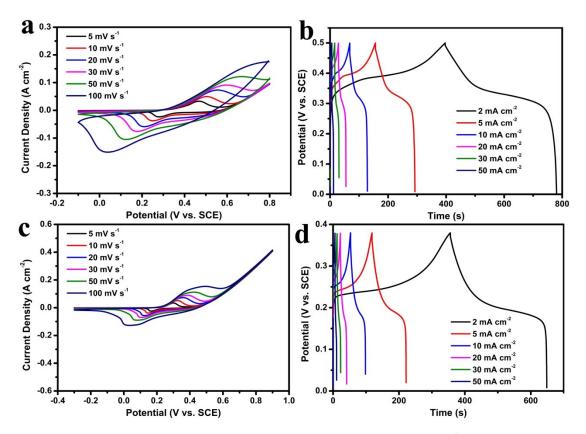


Fig. S1 SEM images of sample. (a,b) rGO/NF, inset: bare NF; (c,d) NiCo<sub>2</sub>O<sub>4</sub>/rGO/NF.



**Fig. S2** (a) CV curves of the  $Co_3S_4/rGO/NF$  at different scanning rates. (b) GCD curves of the  $Co_3S_4/rGO/NF$  at different current densities. (c) CV curves of the NiCo<sub>2</sub>O<sub>4</sub>/rGO/NF at different scanning rates. (d) GCD curves of the NiCo<sub>2</sub>O<sub>4</sub>/rGO/NF at different current densities.

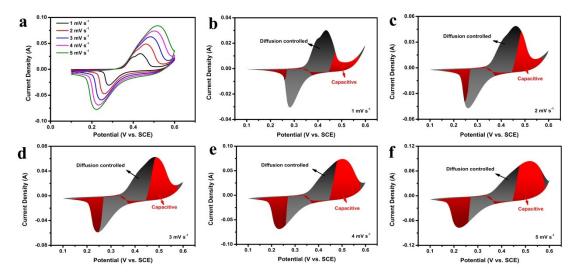
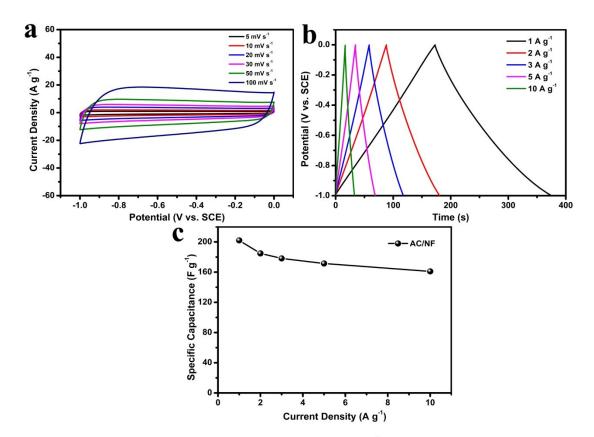


Fig. S3 (a) CV curves of the  $Co_3S_4$ @NiCo\_2O\_4/rGO/NF at different scanning rates. CV curves with capacitive fraction shown by the shaded area at a scan rate at (b) 1 mV s<sup>-1</sup>, (c) 2 mV s<sup>-1</sup>, (d) 3 mV s<sup>-1</sup>, (e) 4 mV s<sup>-1</sup> and (f) 5 mV s<sup>-1</sup>.



**Fig. S4** (a) CV curves of the AC at different scanning rates. (b) GCD curves of the AC at different current densities. (c) Specific capacitances of the AC at different current densities.